

# RB751CS-40-HAF

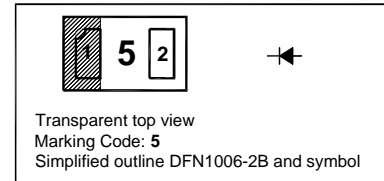
## Silicon Epitaxial Planar Schottky Barrier Diode

### Features

- Small surface mounting type
- Low forward voltage
- High reliability
- Halogen and Antimony Free(HAF), RoHS compliant

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	40	V
Reverse Voltage	$V_R$	30	V
Average Rectified Forward Current	$I_{F(AV)}$	30	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	$I_{FSM}$	200	mA
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 40 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

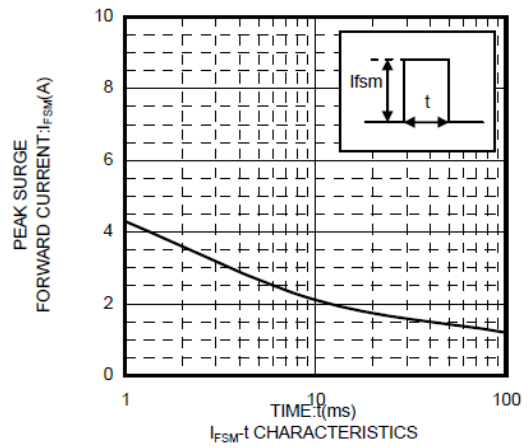
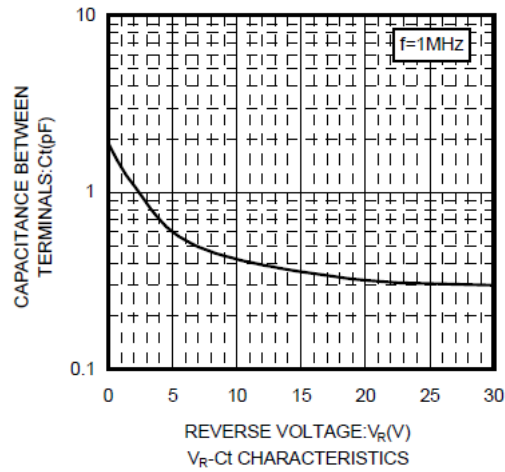
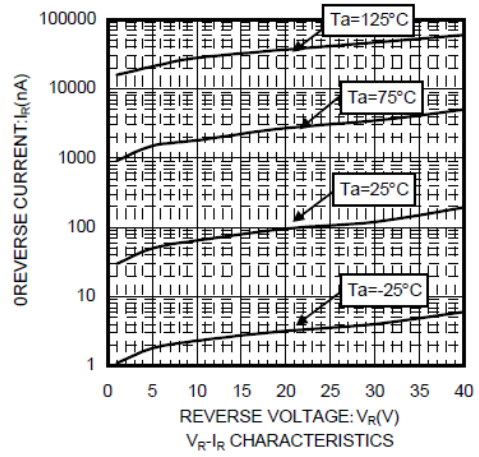
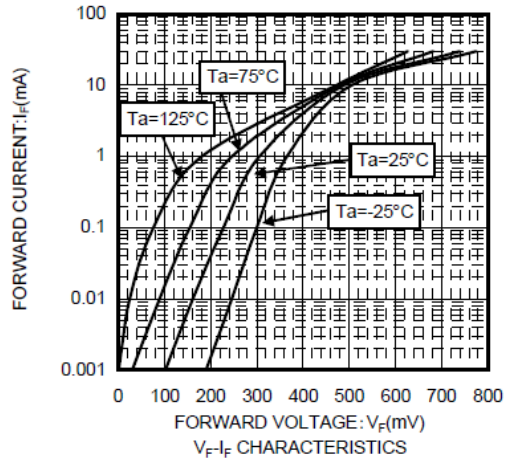
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$	$V_F$	-	0.37	V
Reverse Current at $V_R = 30 \text{ V}$	$I_R$	-	0.5	$\mu\text{A}$
Capacitance Between Terminals at $V_R = 1 \text{ V}$ , $f = 1 \text{ MHz}$	$C_T$	2	-	pF

**TOP DYNAMIC**



Dated: 10/11/2015 Rev: 02

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**TOP DYNAMIC**



ISO14001 : 2004 Certificate No. 121505007  
 ISO 9001 : 2008 Certificate No. 50114012  
 OHSAS 18001 : 2007 Certificate No. 05131508006  
 IECQ QC 080000 Certificate No. ECA11000191002

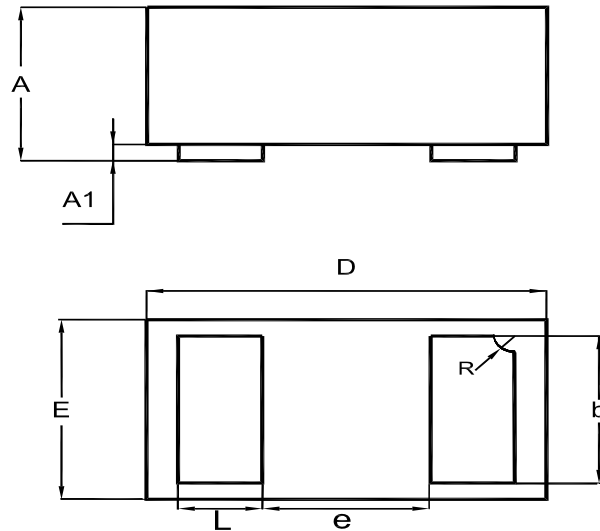
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## PACKAGE OUTLINE

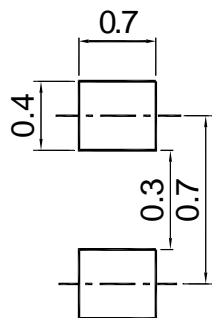
Plastic surface mounted package;

DFN1006-2B



UNIT	A	A1	b	D	E	e	L	R
mm	0.40 0.36	0.05 0	0.55 0.45	1.05 0.95	0.65 0.55	0.4	0.3 0.2	0.15 0.05

## Recommended Soldering Footprint



## Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN1006-2B	8	4 ± 0.1	0.157 ± 0.004	178	7	5,000

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